

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

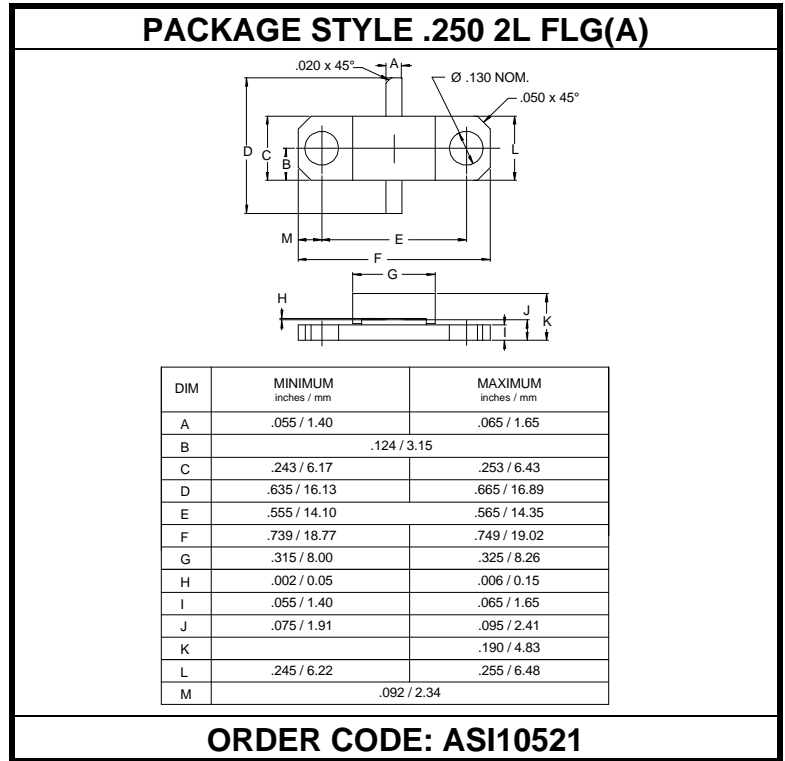
The **ASI ASAT30** is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	10 A
V_{CB}	60 V
V_{CE}	35 V
P_{DISS}	140 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	3.5 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 50 mA	35			V
BV_{CER}	I _C = 50 mA R _{BE} = 10 Ω	60			V
BV_{EBO}	I _E = 10 Ma	4.0			V
I_{CES}	V _E = 28 V			5	mA
h_{FE}	V _{CE} = 5.0 V I _C = 1.0 A	10		100	---
P_{GE}	V _{CC} = 28 V P _{OUT} = 30 W f = 1.65	9.0			dB
η_C	V _{CC} = 28 V P _{OUT} = 30 W f = 1.65	50			%